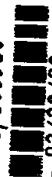


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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10085903	02 28 2002	257		2875	

**APPLICANTS: Wei Andy, Sultan Akif, Wu, David

**CONTINUING DATA VERIFIED:

** FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input checked="" type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed		<input type="checkbox"/> yes <input checked="" type="checkbox"/> no	ATTORNEY DOCKET NO
35 USC 119 conditions met		<input type="checkbox"/> yes <input checked="" type="checkbox"/> no	AMDI.115 HON
Verified and Acknowledged Examiner/Assistant			
TITLE : SOI mosfet junction degradation using multiple buried amorphous layers			

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg.
		Print Fig.	
Primary Examiner			
PREPARED FOR ISSUE		Application Examiner	
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